

### DESCRIPTION

The A4778 is an integrated power switch for self-powered and bus-powered Universal Serial Bus (USB) applications. Several protection functions include current limit and thermal shutdown to prevent catastrophic switch failure caused by increasing power dissipation when continuous heavy load or short circuit occur.

A built-in  $52m\Omega$  P-channel MOSFET with true shutdown function to eliminate any reversed current flowing across the switch when the device is powered off. When the output voltage is higher than input voltage, the power switch will be turned off by the internal output reverse-voltage comparator.  $\overline{FLG}$  is an open-drain output, which reports over-current or over-temperature event and has a typical 8ms deglitch timeout period. In addition,  $\overline{FLG}$  also has typical 3ms deglitch timeout period and reports output reverse-voltage condition.

The A4778 is available in SOT-25 and MSOP8 Packages.

### ORDERING INFORMATION

Package Type		Part Number
SOT-25	E5	A4778ZE5R-TD
SPQ: 3,000pcs/Reel	<b>⊑</b> 3	A4778ZE5VR-TD
MSOP8	MS8	A4778ZMS8R-TD
SPQ: 3,000pcs/Reel	IVISO	A4778ZMS8VR-TD
Note	A: 1.9 F: 2.5 T: Activ H: Hig D: Outp N: No Y: Ou V: Halo	
AiT provides all Ro	HS produ	ucts

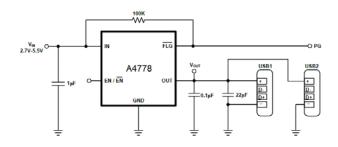
### **FEATURES**

- "Best-in-Class" Quiescent Supply Current
- A4778A: 1.5 A Continuous Current
- A4778E: 2.1 A Continuous Current
- A4778F: 2.5 A Continuous Current
- 52mΩ High-side P-channel MOSFET Switch
- Available with Three Versions Built-in Current Limits
- Operating Range: 2.7V to 5.5V
- 0.2ms Typical Rise Time
- Fast Over-current Response 5µs (typ.)
- Under Voltage Lockout
- 1μA Maximum Shutdown Supply Current
- No Reverse Current when Power Off
- Output Reverse-voltage Protection
- Deglitched Open-drain Over-current Flag Output
- Enable Logic: Active-high or Active-low Versions
- Optional Feature: Output Auto Discharge
- Available in SOT-25 and MSOP8 Packages

### **APPLICATION**

- High-Side Power Protection Switch
- USB Host and Self-Powered Hubs
- USB Bus-Powered Hubs
- Set Top Box
- Smart TV
- MID and Notebook Computer

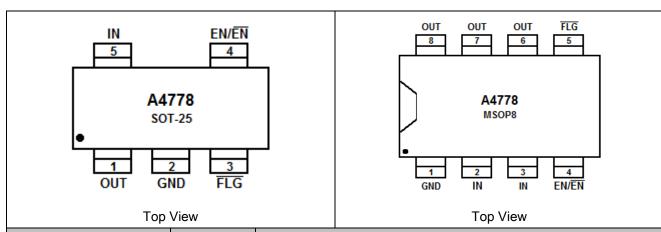
### TYPICAL APPLICATION



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# PIN DESCRIPTION



Pin#		Cumhal	Function		
SOT-25	MSOP8	Symbol	FullClion		
4			Switch Output: Connected to the drain of the internal MOSFET.		
1 6,7,8		OUT	Typically connect to switched side of load.		
2	1	GND	Ground.		
3	5	FLG	Open-drain Fault Flag Output. 3ms delay for thermal shutdown.		
4	4	EN(EN)	Enable: Logic level enable input. Make sure EN pin never floating.		
5 2,3 IN		INI	Input Supply: Connected to the Source of the internal MOSFET		
		IIN	and provides internal DC current to operate the control circuitry.		

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## **ABSOLUTE MAXIMUM RATINGS**

IN	-0.3V ~ 7V
OUT	-0.3V ~ V <sub>IN</sub>
EN/EN	$-0.3V \sim V_{IN} + 0.3V$
FLG	$-0.3V \sim V_{IN} + 0.3V$
ESD Rating per ESDA/JEDEC JDS-001-2014	
Human Body Mode	±6kV <sup>NOTE1</sup>
ESD Ratings per IEC61000-4-2NOTE2	
Contact Discharge	±8kV
Air Discharge	±15kV
Package Thermal Resistance NOTE3	
θ <sub>JA</sub> , SOT-25	250°C/W
θ <sub>JA</sub> , MSOP8	200°C/W
θ <sub>JC</sub> , SOT-25	60°C/W
θ <sub>JC</sub> , MSOP8	55°C/W
Continuous Power Dissipation (T <sub>A</sub> = 25°C)	
SOT-25	0.5W
MSOP8	0.6W
Max Junction TemperatureNOTE4	150°C
T <sub>S</sub> , Storage Temperature	-65°C ~ +150°C
Lead Temperature (Soldering 10 sec.)	260°C

Stress beyond above listed "Absolute Maximum Ratings" may lead permanent damage to the device. These are stress ratings only and operations of the device at these or any other conditions beyond those indicated in the operational sections of the specifications are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## **OPERATING RATINGS**

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V <sub>IN</sub>	2.7	5.5	V
Operating Temperature	T <sub>A</sub>	-40	85	°C

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# ELECTRICAL CHARACTERISTICSNOTE5

Parameter	Symbol	Conditions		Min	Тур.	Max	Unit
Input Supply Voltage	·						
Input Voltage	Vin			2.7	-	5.5	V
Quiescent Current	I <sub>IN_ON</sub>	V <sub>IN</sub> =5.5V, I <sub>OUT</sub> =	0mA	-	30	-	μΑ
Shutdown Current	I <sub>IN_OFF</sub>	V <sub>IN</sub> =5.5V, I <sub>OUT</sub> =	0mA	-	0.1	1	μΑ
Output Leakage Current	ILEAKAGE	V <sub>OUT</sub> =5.5V, V <sub>IN</sub> =	0V	-	2	5	μΑ
UVLO Threshold	V <sub>UVLO_ON</sub>	V <sub>IN</sub> Rising		-	2.45	2.60	V
UVLO Hysteresis	V <sub>UVLO_HYS</sub>			-	25	-	mV
Power switch	•						
Output MOSFET	R <sub>DS(ON)</sub>	I <sub>LOAD</sub> =1A		30	52	85	mΩ
Enable and Soft-start	•						
Enable High Level Threshold	V <sub>EN_H</sub>	V <sub>IN</sub> =5.5V		1.2	-	-	V
Enable Low Level Threshold	V <sub>EN_L</sub>	V <sub>IN</sub> =2.5V		-	-	0.7	V
EN Input Current	I <sub>EN</sub>	V <sub>EN</sub> =5.5V or 0V		-0.5	5	10	μΑ
Turn-On Time	ton	C <sub>L</sub> =1μF, R <sub>LOAD</sub> =100Ω		-	0.2	-	ms
Turn-Off Time	t <sub>OFF</sub>	$C_L=1\mu F, R_{LOAD}=100\Omega$		-	0.3	-	ms
Output and Current Limit	•						
		V <sub>IN</sub> = 5V, V <sub>OUT</sub> =3.5V	A4778F	3.1	3.2	3.7	Α
Over Current CC Regulation	I <sub>LIMIT</sub>		A4778E	2.6	2.75	2.9	Α
			A4778A	1.8	2.0	2.2	Α
Reverse Voltage Protection	V <sub>REVERSE</sub>	V <sub>OUT</sub> -V <sub>IN</sub>		5	20	50	mV
Reverse Current Protection	I <sub>REVERSE</sub>			0.1	0.4	1	Α
Output Rise Time	<b>t</b> <sub>R</sub>	C <sub>OUT</sub> =1μF, R <sub>LOAD</sub> =100Ω		-	0.1	-	ms
Output Fall Time	t <sub>F</sub>	C <sub>OUT</sub> =1μF, R <sub>LOAD</sub> =100Ω		-	0.3	-	ms
Output Auto Discharge		Optional feature,					
Resistance	Rout	$V_{IN} = 5V$ , $V_{OUT} = 5V$ ,		-	300	-	Ω
1 (CSISIALIOE		Shutdown Mode					

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Parameter	Symbol	Conditions	Min	Тур.	Max	Unit	
FAULT FLAG FLG							
Output low Voltage	V <sub>FLG_LOW</sub>	I <sub>FLG</sub> =1mA	-	-	180	mV	
Continuous Sink Current	I <sub>FLG_SINK</sub>		-	-	10	mA	
Off-state Leakage	I <sub>FLG_LEAKAGE</sub>		-	-	1	μΑ	
FLG Deglitch Time	t <sub>FLG</sub>		-	8	-	ms	
Thermal Shutdown							
Thermal Shutdown	T <sub>SD</sub>			150		°C	
Threshold <sup>NOTE6</sup>	ISD		-	150	1	C	
Thermal Shutdown	Т			20		°C	
Hysteresis NOTE6	T <sub>SD_HYS</sub>		-	20	1	C	
Thermal shutdown Threshold in	T			130		°C	
Current Limit NOTE6	TCURRENT_LIMIT		_	130	-	C	

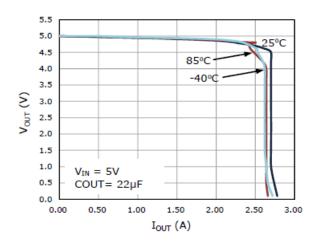
- NOTE1: Class 3A per ESDA/JEDEC JDS-001-2014 classification.
- NOTE2: Output was surged on the EVM with input and output bypassing per the Typical Application Circuit on the first page with no device failures
- NOTE3: Thermal Resistance is measured in the natural convection at TA = 25 °C on a low effective single layer thermal conductivity test board of JEDEC 51-3 thermal measurement standard.
- NOTE4:  $T_J$  is calculated from the ambient temperature  $T_A$  and power dissipation  $P_D$ .
- NOTE5: 100% production test at +25°C. Specifications over the temperature range are guaranteed by design and characterization. The device is not guaranteed to function outside its operating conditions.
- NOTE6: Guaranteed by design and characterization only.

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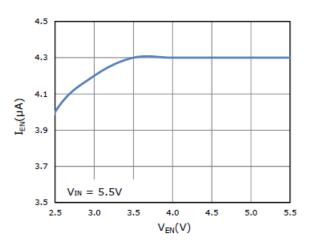


## TYPICAL PERFORMANCE CHARACTERISTICS

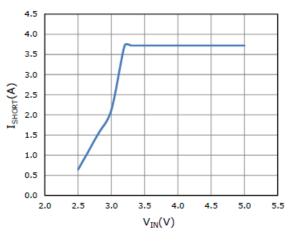
1. Over-current Protection Characteristics (A4778E)



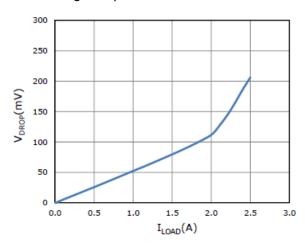
2. I<sub>EN</sub> vs. V<sub>EN</sub> Characteristics



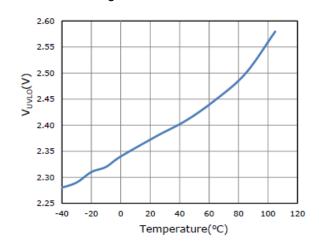
3. Short Circuit Output Current (A4778E)



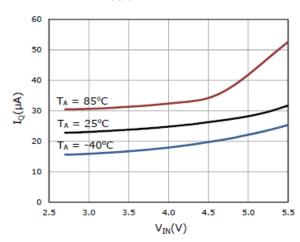
4. Voltage Drop vs. ILOAD



5. UVLO Voltage



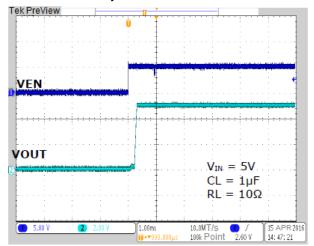
6. Quiescent Supply Current



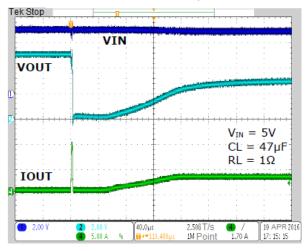
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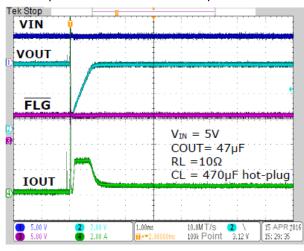
### 7. Turn on Delay Time and Rise Time



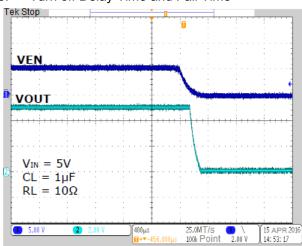
### 9. Resistance Load Inrush Response



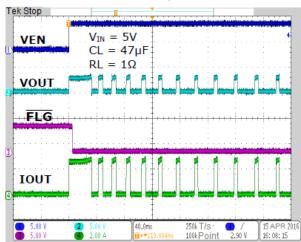
### 11. Capacitance Load Inrush Response



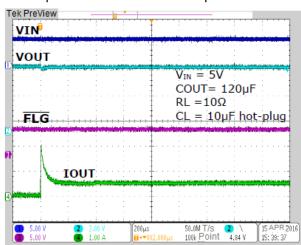
### 8. Turn off Delay Time and Fall Time



### 10. Thermal Shutdown Response



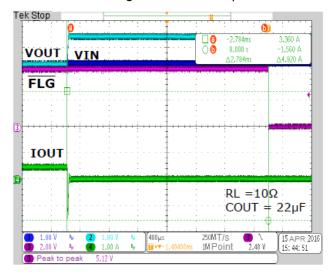
### 12. Capacitance Load Inrush Response



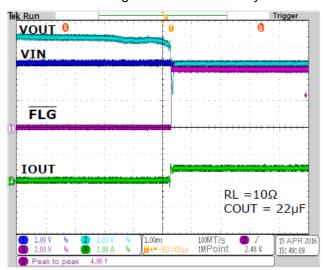
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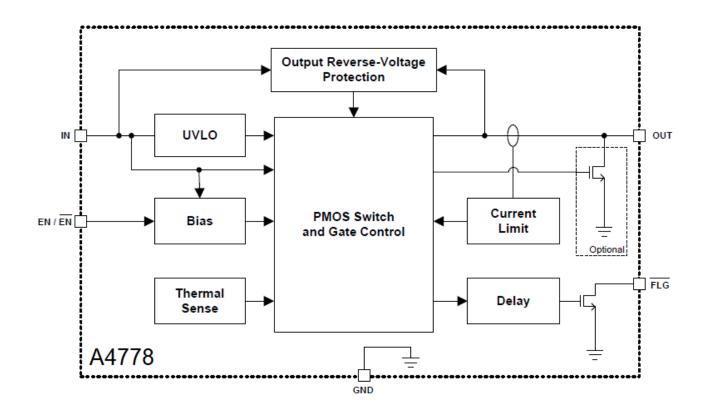
### 13. Reverse-Voltage Protection Response



### 14. Reverse-Voltage Protection Recovery



## **BLOCK DIAGRAM**



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### **DETAILED INFORMATION**

### Input and Output

IN (input) is the power supply connection to the logic circuitry and the source of the internal P-channel MOSFET. OUT (output) is the drain of the internal P-channel MOSFET. In a typical application, current flows through the switch from IN to OUT toward the load.

#### Thermal Shutdown

The A4778 protects itself with two independent thermal sensing circuits that monitor the operating temperature of the power-switch and disables operation if the temperature exceeds recommended operating conditions. The device operates in constant-current mode during an over-current condition, which increases the voltage drop across power-switch. The power dissipation in the package is proportional to the voltage drop across the power-switch, so the junction temperature rises during an over-current condition. The first thermal sensor turns off the power-switch when the die temperature exceeds 130°C and the device is in current limit. The second thermal sensor turns off the power-switch when the die temperature exceeds 150°C regardless of whether the power-switch is in current limit. Hysteresis is built into both thermal sensors, and the switch turns on after the device has cooled down approximately 20°C (thermal shutdown threshold hysteresis in current-limit is 20°C). The switch continues to cycle off and on until the fault is removed. The open-drain FLG is asserted (active low) immediately during an over-temperature shutdown condition.

### **Under-voltage Lockout**

UVLO (under-voltage lockout) prevents the internal MOSFET switch from turning on until  $V_{IN}$  (input voltage) exceeds 2.45V typically. After the switch turns on, if the input voltage drops below 2.425V typically, UVLO shuts off the switch.

### **Output Reverse-Voltage Protection**

The output reverse-voltage protection turns off the MOSFET switch whenever the output voltage is higher than the input voltage by 20mV (typ.) and the MOSFET switch will turn on when output reverse-voltage condition is removed.

### FLG Function

The FLG open-drain output is asserted (active low) when an over current condition is encountered after a 8ms deglitch timeout. The typical trigger point of A4778F is above 2.6A, A4778E is above 2.2 A, A4778A is above 1.6A. The FLG output remains asserted until the overcurrent condition is removed. Over temperature

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condition is also reported by  $\overline{\text{FLG}}$  open-drain output. In addition,  $\overline{\text{FLG}}$  is also asserted in output reverse-voltage condition.

### Supply Filtering

A 1 $\mu$ F bypass capacitor from IN pin to GND pin, located near the A4778, is strongly recommended to control supply transients. Without a bypass capacitor, an output short may cause sufficient ringing on the input (from supply lead inductance) to damage internal control circuitry. Input transients must not exceed the absolute maximum supply voltage ( $V_{IN\_MAX} = 7V$ ) even for a short duration.

### **Enable Input**

EN (enable) must be driven by a logic high or logic low for a clearly defined input. Floating the input may cause unpredictable operation. EN should not be allowed to go negative with respect to GND.

#### **Short Circuit Condition**

The current limit circuitry prevents the power-switch from damage due to overcurrent. When a heavy load or short circuit is applied to the output, a large transient current may flow through until the circuitry responses. Once the circuitry responds, it limits the output current to I<sub>SC</sub>. Since the current-sense amplifier is overdriven during this time and the power-switch is disabled momentarily, the output current drops to nearly zero. The current-sense amplifier recovers and ramps the output current to I<sub>OS</sub>. The output current keep at I<sub>OS</sub> until the short circuit condition is removed or the device begins to thermal cycle. The duration and the amplitude of the large transient current at short circuit moment vary with the measurement setup and the external components, especially ESR of input capacitor. Figure 2 shows the recommended setup to measure the short circuit characteristic. The 'Short Device' in Figure 2 should be a low R<sub>DS(ON)</sub>, high current and low gate charge N-channel MOSFET to simulate the real situation.

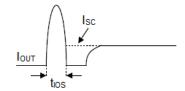


Figure 1. Output Current at Short Circuit Moment

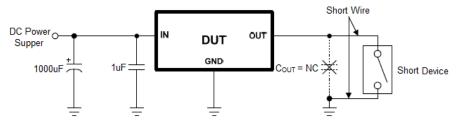


Figure 2. Setup to Measure the Short Circuit Characteristic

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#### Note:

In order to identify the short circuit characteristic of the IC, avoid the interferences of parasitic inductor, output capacitor and contact resistance. It is recommended following the procedures below:

- 1. Add 1000 $\mu F$  of capacitor between  $V_{IN}$  and GND, and close to IC.
- 2. Remove output capacitor.
- 3. Short the output by using the Short Device.
- 4. Measure output current (I<sub>OUT</sub>).

### **Layout Considerations**

For best performance of the A4778 series, the following guidelines must be strictly followed:

- 1. Input and output capacitors should be placed close to the device and connected to ground plane to reduce noise coupling.
- 2. The GND pin should be connected to a strong ground plane for heat sink.
- 3. Keep the main current traces as short as possible and wide.

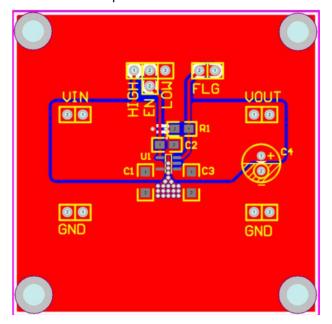
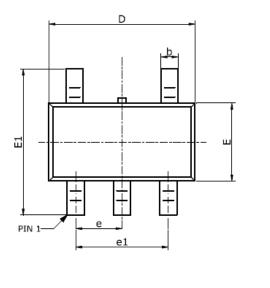


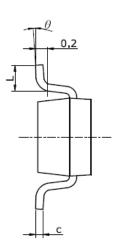
Figure 3. Recommended PCB Layout

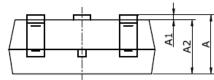
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# PACKAGE INFORMATION

Dimension in SOT-25 (Unit: mm)



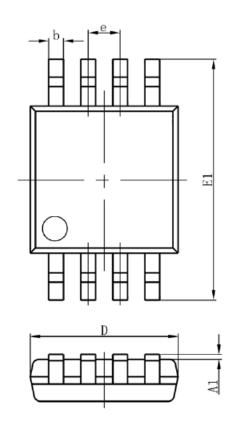


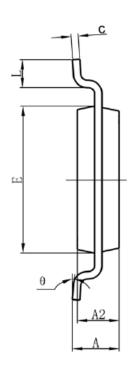


Cymphol	Millim	neters	Inches		
Symbol	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.850	3.050	0.112	0.120	
Е	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950	(BSC)	0.037(BSC)		
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

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## Dimension in MSOP8 (Unit: mm)





Cymphol	Millim	eters	Inches		
Symbol	Min	Max	Min	Max	
Α	0.820	1.100	0.032	0.043	
A1	0.020	0.150	0.001	0.006	
A2	0.750	0.950	0.030	0.037	
b	0.250	0.380	0.010	0.015	
С	0.090	0.230	0.004	0.009	
D	2.900	3.100	0.114	0.122	
е	0.650(BSC)		0.026(BSC)		
Е	2.900	3.100	0.114	0.122	
E1	4.750	5.050	0.187	0.199	
L	0.400	0.800	0.016	0.031	
θ	0°	6°	0°	6°	

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